FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. IMEC280.001AUS	APPLICATION NO. 10/621,044
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	APPLICANT Collaert, et al.	
	FILING DATE July 15, 2003	GROUP ~~2814~~ 2823

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
T.D	1	6,118,161	09/12/00	Chapman, et al.			
T.D	2	6,207,511	03/27/01	Chapman, et al.			
T.D	3	6,252,284 B1	06/26/01	Muller, et al.			

EXAMINER INITIAL		OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
T.D	4	Choi, et al., "Nanoscale CMOS Spacer FinFET for the Terabit Era", IEEE Electron Device Letters, vol. 23, no. 1, pp. 25-27, (January 2002).
	5	Choi, et al., "Sub-20nm CMOS FinFET Technologies", IEEE, pp. 421-424, (2001).
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	7	Huang, et al., "Sub-50 nm P-Channel FinFET", IEEE Transactions on Electron Devices, vol. 48, no. 5, pp. 880-886, (May 2001).
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T.D	9	European Search Report dated December 17, 2002 for European Application No. 02 44 7135.1.

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EXAMINER T. DANG	DATE CONSIDERED 12/12/04

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